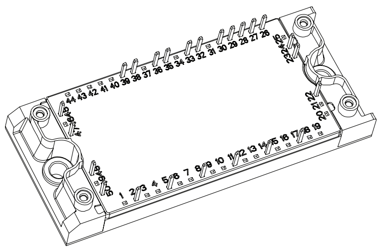
IGBT PIM Module, 25 A



ECONO2 PIM

FEATURES

- Low $V_{CE(on)}$ non punch through IGBT technology
- Low diode V_F
- 10 µs short circuit capability
- Square RBSOA
- HEXFRED® antiparallel diode with ultrasoft reverse recovery characteristics
- Positive $V_{CE(on)}$ temperature coefficient
- Ceramic DBC substrate
- Low stray inductance design
- Speed 8 to 60 kHz
- Totally lead (Pb)-free
- Designed and qualified for industrial market

Pb-free
RoHS COMPLIANT

BENEFITS

- Benchmark efficiency for motor control
- Rugged transient performance
- Low EMI, requires less snubbing
- Direct mounting to heatsink
- PCB solderable terminals
- Low junction to case thermal resistance

PRODUCT SUMMARY	
V_{CES}	1200 V
$V_{CE(on)}$	2.4 V
t_{sc} at T_J = 150 °C	> 10 µs
I_C at T_C = 80 °C	25 A

ABSOLUTE MAXIMUM RATINGS

	PARAMETER	SYMBOL	TEST CONDITIONS		MAX.	UNITS
Inverter	Collector to emitter voltage	V_{CES}			1200	V
	Gate to emitter voltage	V_{GES}			± 20	
	Continuous collector current	I_C	T_C = 25 °C		40	A
			T_C = 80 °C		25	
	Pulsed collector current See fig. C.T.5	I_{CM}			80	A
	Diode maximum forward current	I_{FM}	Pulsed		80	A
	Power dissipation	P_D	One IGBT	25 °C	198	W
Input rectifier	Repetitive peak reverse voltage	V_{RRM}			1600	V
	Average output current	$I_{F(AV)}$	50/60 Hz sine pulse	80 °C	20	A
	Surge current (non-repetitive)	I_{FSM}	Rated V_{RRM} applied, 10 ms, sine pulse		250	
	I^2t (non-repetitive)	I^2t			316	A^2s
Brake	Collector to emitter voltage	V_{CES}			1200	V
	Gate to emitter voltage	V_{GES}			± 20	
	Continuous collector current	I_C	T_C = 25 °C		40	A
			T_C = 80 °C		25	
	Pulsed collector current See fig. C.T.5	I_{CM}			80	A
	Power dissipation	P_D	One IGBT	25 °C	198	W
	Maximum operating junction temperature	T_J			150	°C
	Storage temperature range	T_{Stg}			- 40 to + 125	
	Isolation voltage	V_{ISOL}	AC (1 min)		2500	V

ELECTRICAL SPECIFICATIONS (T_J = 25 °C unless otherwise noted)							
	PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Inverter IGBT	Collector to emitter breakdown voltage	$BV_{(CES)}$	V_{GE} = 0 V, I_C = 500 µA	1200	-	-	V
	Temperature coefficient of breakdown voltage	$\Delta V_{(BR)CES}/\Delta T_J$	V_{GE} = 0 V, I_C = 1 mA (25 °C to 125 °C)	-	1.0	-	V/°C
	Collector to emitter voltage	$V_{CE(on)}$	I_C = 25 A, V_{GE} = 15 V	-	2.40	2.70	V
			I_C = 40 A, V_{GE} = 15 V	-	2.95	3.30	
			I_C = 25 A, V_{GE} = 15 V, T_J = 125 °C	-	2.85	-	
			I_C = 40 A, V_{GE} = 15 V, T_J = 125 °C	-	3.55	-	
	Gate threshold voltage	$V_{GE(th)}$	V_{CE} = V_{GE}, I_C = 250 µA	4.0	5.0	6.0	
	Threshold voltage temp. coefficient	$\Delta V_{GE(th)}/\Delta T_J$	V_{CE} = V_{GE}, I_C = 1 mA (25 °C to 125 °C)	-	- 10	-	mV/°C
	Zero gate voltage collector current	I_{CES}	V_{GE} = 0 V, V_{CE} = 1200 V	-	-	100	µA
			V_{GE} = 0 V, V_{CE} = 1200 V T_J = 125 °C	-	750	-	
	Gate to emitter leakage current	I_{GES}	V_{GE} = ± 20 V	-	-	± 200	nA
	Total gate charge (turn-on)	Q_G	I_C = 25 A V_{CC} = 400 V V_{GE} = 15 V	-	175	265	nC
	Gate to emitter charge (turn-on)	Q_{GE}		-	17.5	30	
	Gate to collector charge (turn-on)	Q_{GC}		-	81	125	
	Turn-on switching loss	E_{on}	I_C = 25 A, V_{CC} = 600 V V_{GE} = 15 V, R_G = 10 Ω, L = 400 µH, T_J = 25 °C [(1)]	-	2.45	4.45	mJ
	Turn-off switching loss	E_{off}		-	2.05	3.20	
	Total switching loss	E_{tot}		-	4.50	7.65	
	Turn-on switching loss	E_{on}	I_C = 25 A, V_{CC} = 600 V V_{GE} = 15 V, R_G = 10 Ω, L = 400 µH, T_J = 125 °C [(1)]	-	3.35	5.65	
	Turn-off switching loss	E_{off}		-	2.85	3.85	
	Total switching loss	E_{tot}		-	6.20	9.50	
	Turn-on delay time	$t_{d(on)}$	I_C = 25 A, V_{CC} = 600 V V_{GE} = 15 V, R_G = 10 Ω, L = 400 µH, T_J = 125 °C	-	80	104	ns
	Rise time	t_r		-	50	70	
	Turn-off delay time	$t_{d(off)}$		-	510	1000	
	Fall time	t_f		-	230	299	
	Input capacitance	C_{ies}	V_{GE} = 0 V V_{CC} = 30 V f = 1 MHz	-	2370	-	pF
	Output capacitance	C_{oes}		-	455	-	
	Reverse transfer capacitance	C_{res}		-	60	-	
Inverter IGBT	Reverse bias safe operating area	RBSOA	T_J = 150 °C, I_C = 80 A R_G = 47 Ω, V_{GE} = 15 V to 0 V	Fullsquare			
	Short circuit safe operating area	SCSOA	I_P = 180 A to 270 A V_{CC} = 900 V R_G = 47 Ω, V_{GE} = 15 V to 0 V	10	-	-	µs
	Diode peak reverse recovery current	I_{rr}	T_J = 125 °C V_{CC} = 600 V, I_F = 25 A, L = 400 µH, R_G = 10 Ω, V_{GE} = 15 V	-	35	-	A
	Diode forward voltage drop	V_{FM}	I_F = 25 A	-	1.90	2.35	V
			I_F = 40 A	-	2.25	2.80	
			I_F = 25 A, T_J = 125 °C	-	2.00	-	
			I_F = 40 A, T_J = 125 °C	-	2.45	-	

ELECTRICAL SPECIFICATIONS (T_J = 25 °C unless otherwise noted)							
	PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNITS**
Input rectifier	Maximum forward voltage drop	V_{FM}	I_F = 25 A	-	-	1.5	V
	Maximum reverse leakage current	I_{RM}	T_J = 25 °C, V_R = 1600 V	-	-	0.1	mA
			T_J = 150 °C, V_R = 1600 V	-	-	1.0	
	Forward slope resistance	r_T	T_J = 150 °C	-	-	10.4	mΩ
	Conduction thresold voltage	$V_{F (TO)}$		-	-	0.85	V
Brake IGBT	Collector to emitter breakdown voltage	$BV_{(CES)}$	V_{GE} = 0 V, I_C = 500 µA	1200	-	-	V
	Temperature coefficient of breakdown voltage	$\Delta V_{(BR)CES}/\Delta T_J$	V_{GE} = 0 V, I_C = 1 mA (25 °C to 125 °C)	-	1.0	-	V/°C
	Collector to emitter voltage	$V_{CE(on)}$	I_C = 25 A, V_{GE} = 15 V	-	2.4	2.7	V
			I_C = 40 A, V_{GE} = 15 V	-	2.95	3.3	
			I_C = 25 A, V_{GE} = 15 V, T_J = 125 °C	-	2.85	-	
			I_C = 40 A, V_{GE} = 15 V, T_J = 125 °C	-	3.55	-	
	Gate threshold voltage	$V_{GE(th)}$	V_{CE} = V_{GE}, I_C = 250 µA	4.0	5.0	6.0	
	Threshold voltage temperature coefficient	$\Delta V_{GE(th)}/\Delta T_J$	V_{CE} = V_{GE}, I_C = 1 mA (25 °C to 125 °C)	-	- 10	-	mV/°C
	Zero gate voltage collector current	I_{CES}	V_{GE} = 0 V, V_{CE} = 1200 V	-	-	100	µA
			V_{GE} = 0 V, V_{CE} = 1200 V T_J = 125 °C	-	750	-	
	Gate to emitter leakage current	I_{GES}	V_{GE} = ± 20 V	-	-	± 200	nA
	Total gate charge (turn-on)	Q_G	I_C = 25 A V_{CC} = 400 V V_{GE} = 15 V	-	175	265	nC
	Gate to emitter charge (turn-on)	Q_{GE}		-	17.5	30	
	Gate to collector charge (turn-on)	Q_{GC}		-	81	125	
	Turn-on switching loss	E_{on}	I_C = 25 A, V_{CC} = 600 V V_{GE} = 15 V, R_G = 102 Ω, L = 400 µH, T_J = 25 °C (1)	-	2.45	4.45	mJ
	Turn-off switching loss	E_{off}		-	2.05	3.20	
	Total switching loss	E_{tot}		-	4.50	7.65	
	Turn-on switching loss	E_{on}	I_C = 15 A, V_{CC} = 600 V V_{GE} = 15 V, R_G = 10 Ω, L = 400 µH, T_J = 125 °C (1)	-	3.35	5.65	
	Turn-off switching loss	E_{off}		-	2.85	3.85	
	Total switching loss	E_{tot}		-	6.20	9.50	
	Turn-on delay time	$t_{d(on)}$	I_C = 25 A, V_{CC} = 600 V V_{GE} = 15 V, R_G = 10 Ω, L = 400 µH, T_J = 125 °C	-	80	104	ns
	Rise time	t_r		-	50	70	
	Turn-off delay time	$t_{d(off)}$		-	510	1000	
	Fall time	t_f		-	230	299	
Brake IGBT	Input capacitance	C_{ies}	V_{GE} = 0 V V_{CC} = 30 V f = 1 MHz	-	2370	-	pF
	Output capacitance	C_{oes}		-	455	-	
	Reverse transfer capacitance	C_{res}		-	60	-	
	Reverse bias safe operating area	RBSOA	T_J = 150 °C, I_C = 80 A R_G = 10 Ω, V_{GE} = 15 V to 0 V	Fullsquare			
	Short circuit safe operating area	SCSOA	T_J = 150 °C V_{CC} = 900 V, V_P = 1200 V R_G = 10 Ω, V_{GE} = 15 V to 0 V	10	-	-	µs

ELECTRICAL SPECIFICATIONS (T_J = 25 °C unless otherwise noted)							
	PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Brake Diode	Diode peak reverse recovery current	I_{rr}	T_J = 125 °C V_{CC} = 600 V, I_F = 25 A, L = 400 µH R_G = 10 Ω, V_{GE} = 15 V	-	35	-	A
	Diode forward voltage drop	V_{FM}	I_F = 25 A	-	1.90	2.35	V
			I_F = 40 A	-	2.25	2.80	
			I_F = 25 A, T_J = 125 °C	-	2.0	-	
			I_F = 40 A, T_J = 125 °C	-	2.45	-	
NTC	Resistance	R	T_J = 25 °C	4538	5000	5495	Ω
			T_J = 100 °C	468.6	493.3	518	
	B value	B	T_J = 25 °C/50 °C	3307	3375	3443	K

Note

(1) Energy losses include "tail" and diode reverse recovery

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS
Junction to case inverter IGBT thermal resistance	R_{thJC}	-	-	0.63	°C/W
Junction to case inverter FRED thermal resistance		-	-	1.0	
Junction to case brake DIODE thermal resistance		-	-	1.0	
Junction to case brake IGBT thermal resistance		-	-	0.63	
Junction to case input rectifier thermal resistance		-	-	0.85	
Case to sink, flat, greased surface	R_{thCS}	-	0.05	-	
Mounting torque (M5)		2.7	-	3.3	Nm
Weight		-	170	-	g

INVERTER

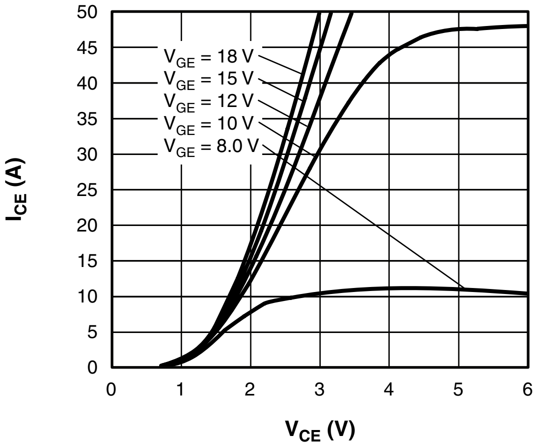


Fig. 1 - Typical IGBT Output Characteristics
T_J = 25 °C; t_p = 80 µs

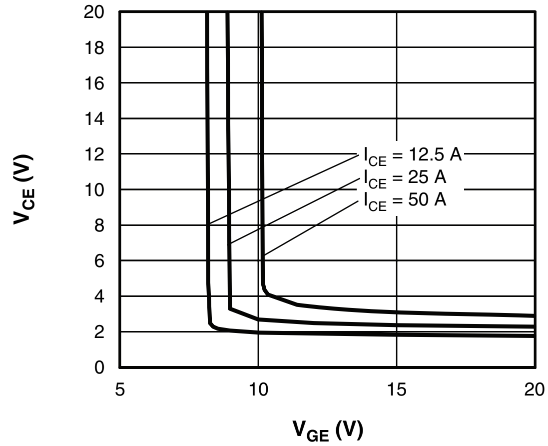


Fig. 4 - Typical V_{CE} vs. V_{GE}
T_J = 25 °C

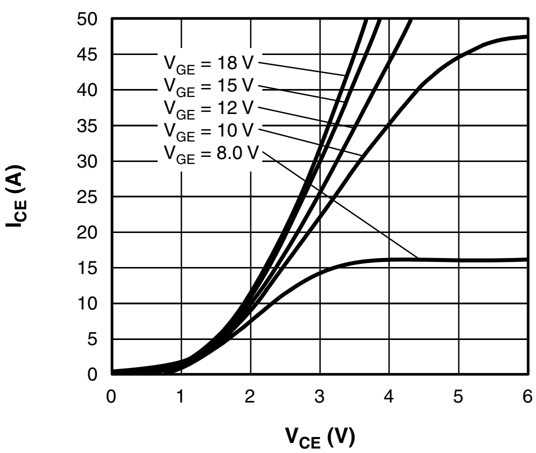


Fig. 2 - Typical IGBT Output Characteristics
T_J = 125 °C, t_p = 80 µs

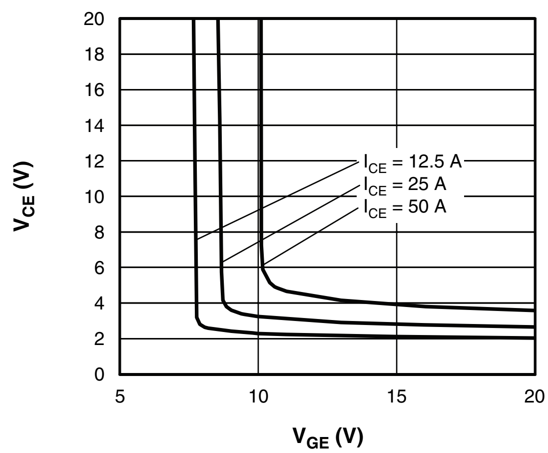


Fig. 5 - Typical V_{CE} vs. V_{GE}
T_J = 125 °C

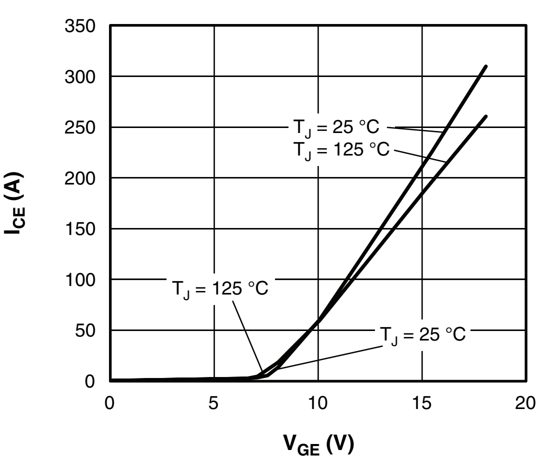


Fig. 3 - Typical Transfer Characteristics
V_{CE} = 50 V; t_p = 10 µs

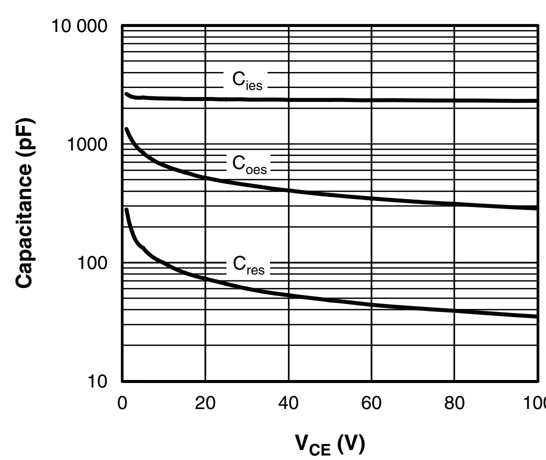


Fig. 6 - Typical Capacitance vs. V_{CE}
V_{GE} = 0 V; f = 1 MHz

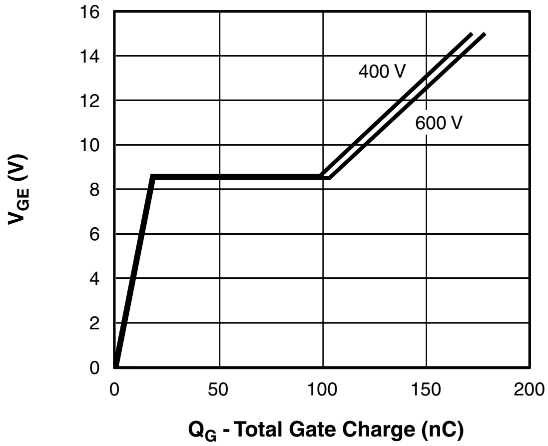


Fig. 7 - Typical Gate Charge vs. V_{GE}
I_{CE} = 25 A; L = 1 mH

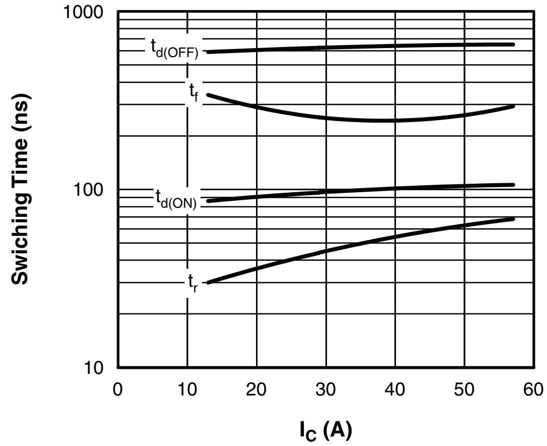


Fig. 10 - Typical Switching Time vs. I_C
T_J = 125 °C; L = 400 µH; V_{CE} = 600 V;
R_G = 10 Ω ; V_{GE} = 15 V

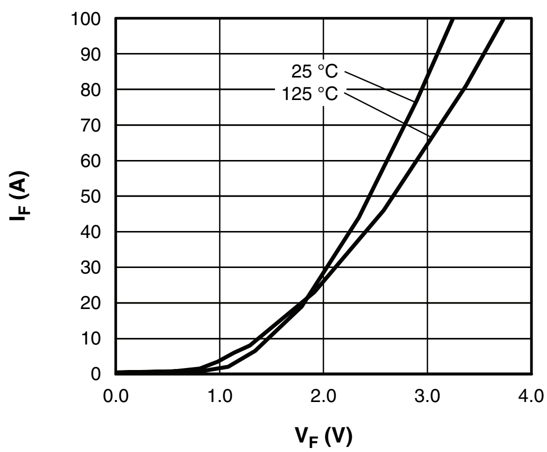


Fig. 8 - Typical Diode Forward Characteristics
t_p = 80 µs

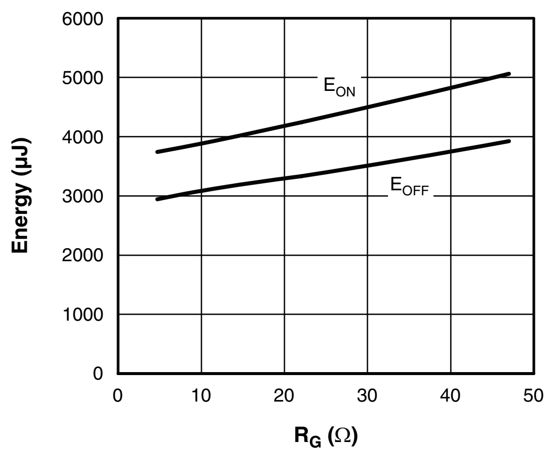


Fig. 11 - Typical Energy Loss vs. R_G
T_J = 125 °C; L = 400 µH; V_{CE} = 600 V;
I_{CE} = 25 A; V_{GE} = 15 V

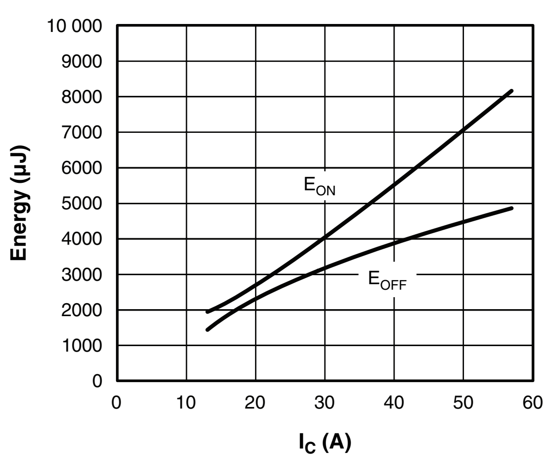


Fig. 9 - Typical Energy Loss vs. I_C
T_J = 125 °C; L = 400 µH; V_{CE} = 600 V;
R_G = 10 Ω; V_{GE} = 15 V

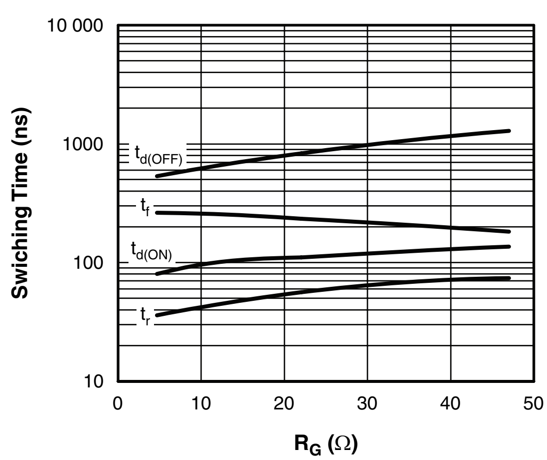


Fig. 12 - Typical Switching Time vs. R_G
T_J = 125 °C; L = 400 µH; V_{CE} = 600 V;
I_{CE} = 25 A; V_{GE} = 15 V

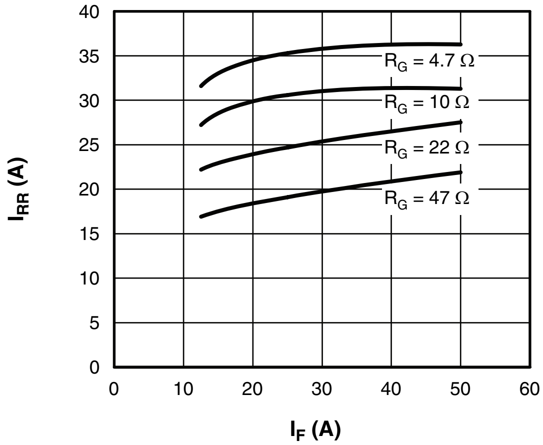


Fig. 13 - Typical Diode I_{RR} vs. I_F
T_J = 125 °C

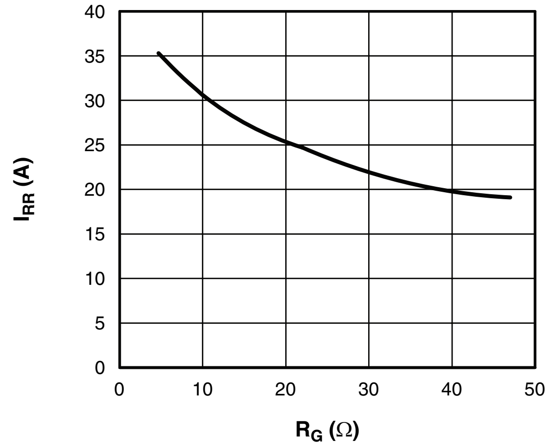


Fig. 14 - Typical Diode I_{RR} vs. R_G
T_J = 125 °C; I_F = 25 A

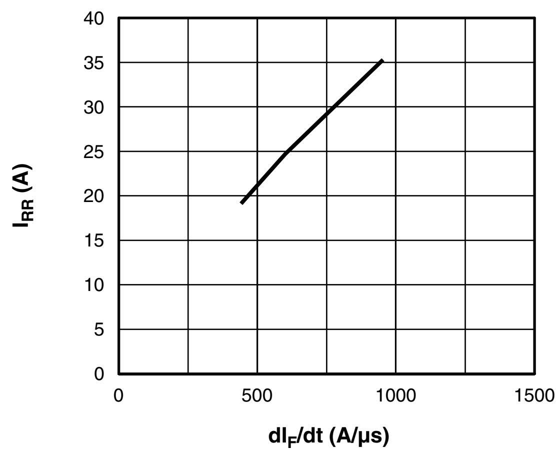


Fig. 15 - Typical Diode I_{RR} vs. dI_F/dt
V_{CC} = 600 V; V_{GE} = 15 V; I_F = 25 A; T_J = 125 °C

THERMISTOR

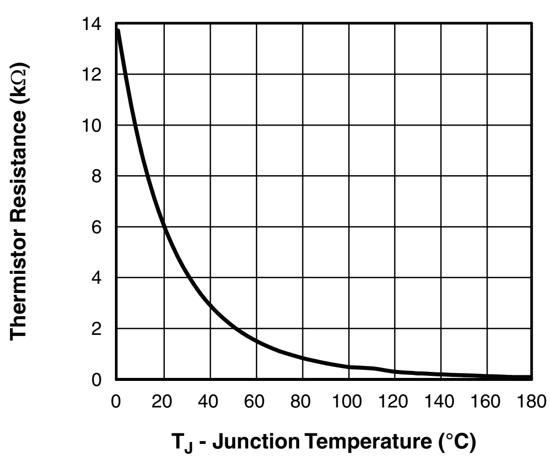


Fig. 16 - Thermistor Resistance vs. Temperature

INPUT RECTIFIER

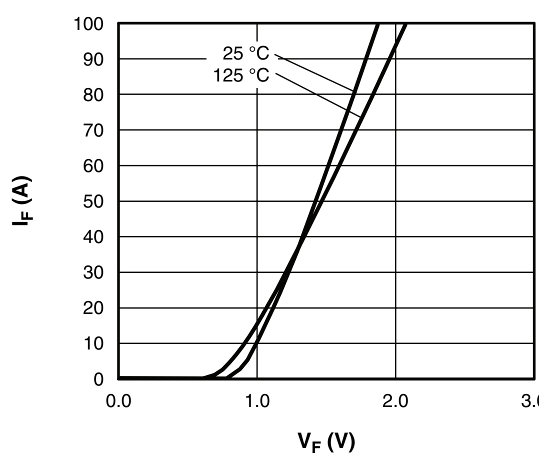


Fig. 17 - Typical Diode Forward Characteristics
t_p = 80 µs

INVERTER

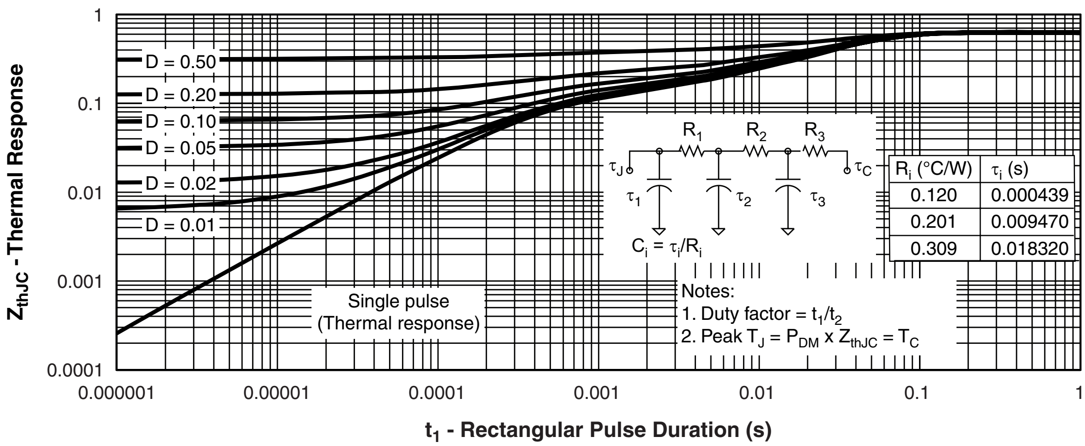


Fig. 18 - Maximum Transient Thermal Impedance, Junction to Case (Inverter IGBT)

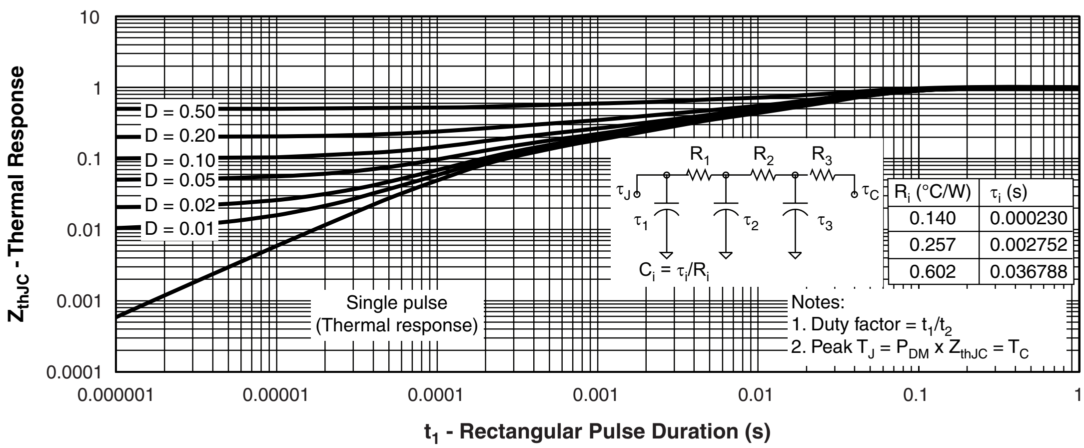


Fig. 19 - Maximum Transient Thermal Impedance, Junction to Case (Inverter FRED)

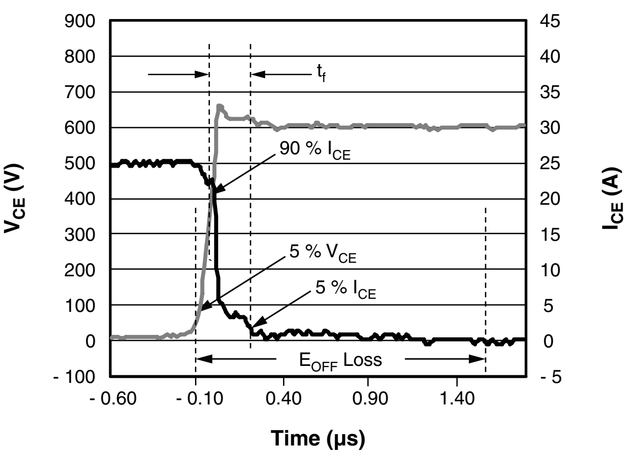


Fig. WF1 - Typical Turn-Off Loss Waveform at T_J = 125 °C using Fig. C.T.4

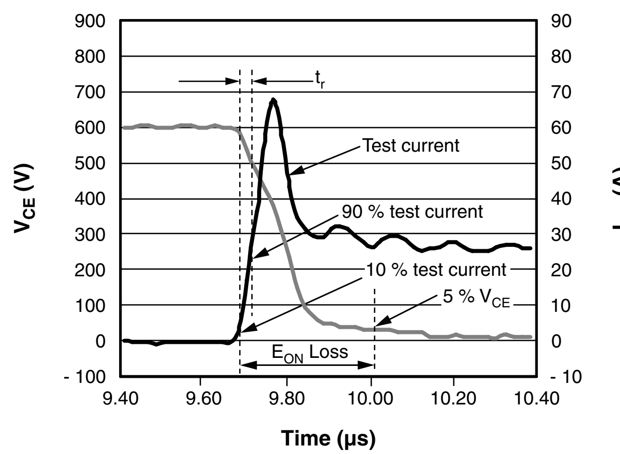


Fig. WF2 - Typical Turn-Off Loss Waveform at T_J = 125 °C using Fig. C.T.4

BRAKE

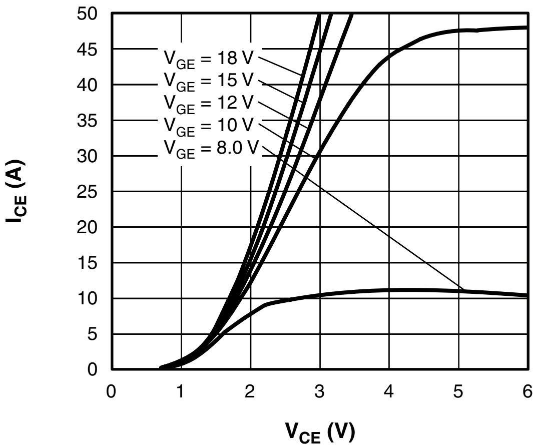


Fig. 20 - Typical IGBT Output Characteristics
T_J = 25 °C; t_p = 80 µs

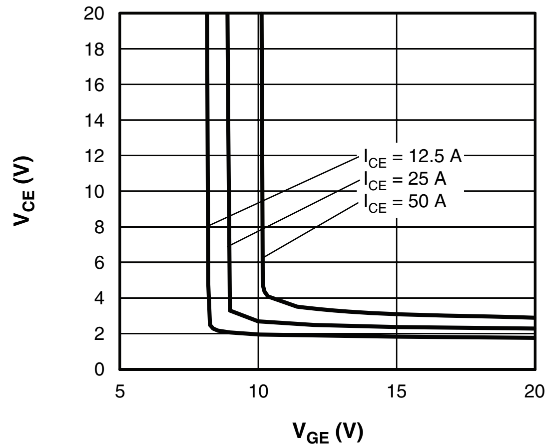


Fig. 23 - Typical V_{CE} vs. V_{GE}
T_J = 25 °C

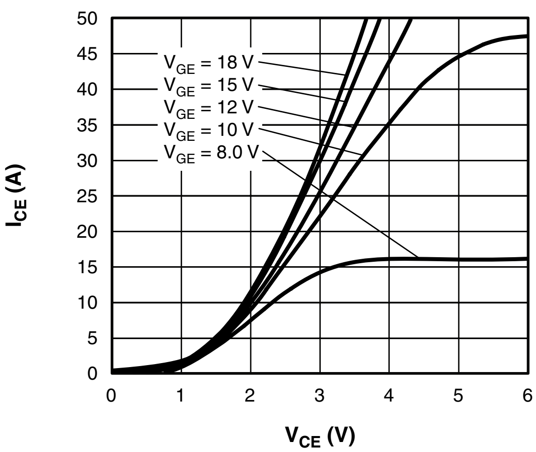


Fig. 21 - Typical IGBT Output Characteristics
T_J = 125 °C; t_p = 80 µs

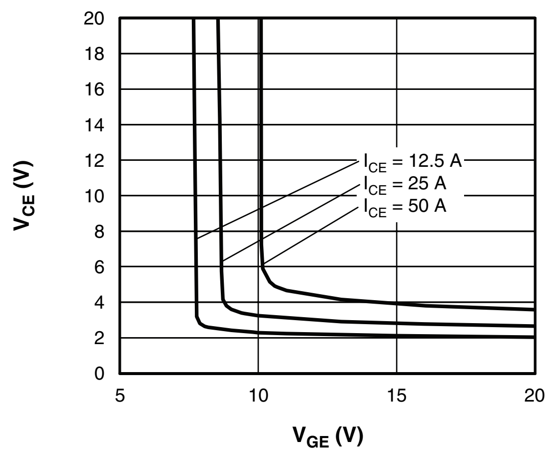


Fig. 24 - Typical V_{CE} vs. V_{GE}
T_J = 125 °C

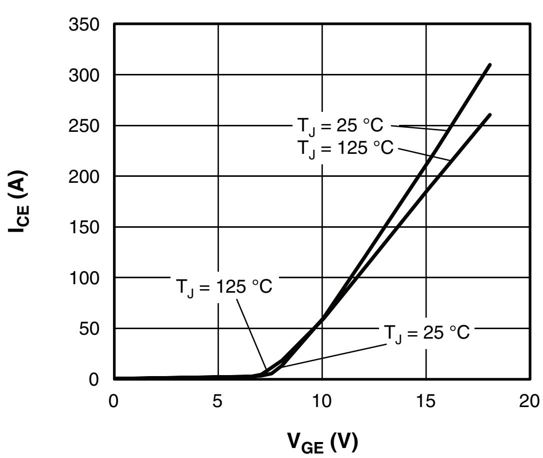


Fig. 22 - Typical Transfer Characteristics
V_{CE} = 50 V; t_p = 10 µs

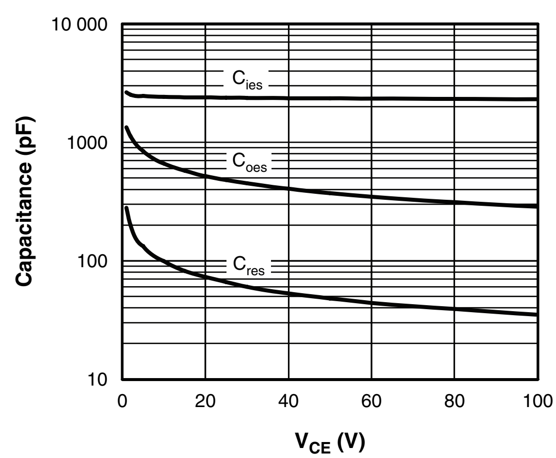


Fig. 25 - Typical Capacitance vs. V_{CE}
V_{GE} = 0 V; f = 1 MHz

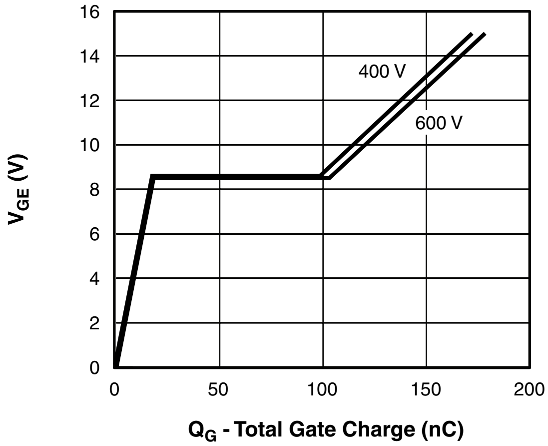


Fig. 26 - Typical Gate Charge vs. V_{GE}
I_{CE} = 25 A; L = 1 mH

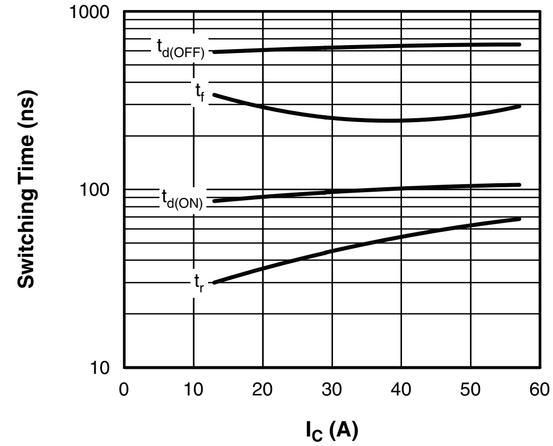


Fig. 29 - Typical Switching Time vs. I_C
T_J = 125 °C; L = 400 µH; V_{CE} = 600 V; R_G = 10 Ω; V_{GE} = 15 V

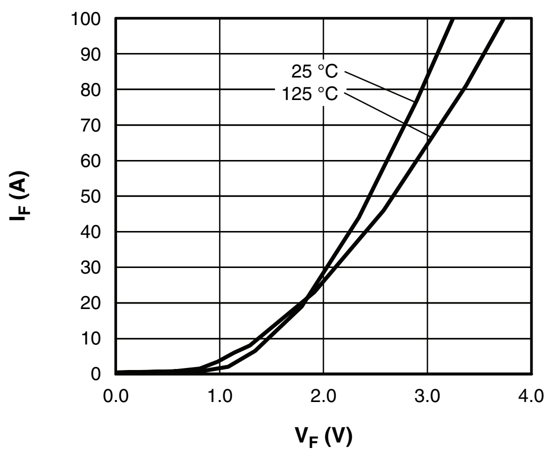


Fig. 27 - Typical Diode Forward Characteristics
t_p = 80 µs

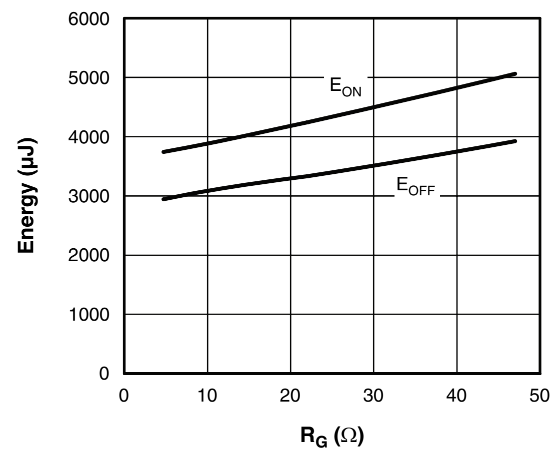


Fig. 30 - Typical Energy Loss vs. R_G
T_J = 125 °C; L = 400 µH; V_{CE} = 600 V; I_{CE} = 25 A; V_{GE} = 15 V

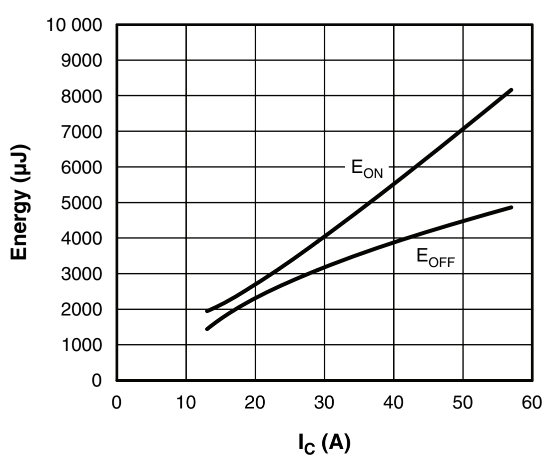


Fig. 28 - Typical Energy Loss vs. I_C
T_J = 125 °C; L = 400 µH; V_{CE} = 600 V; R_G = 10 Ω; V_{GE} = 15 V

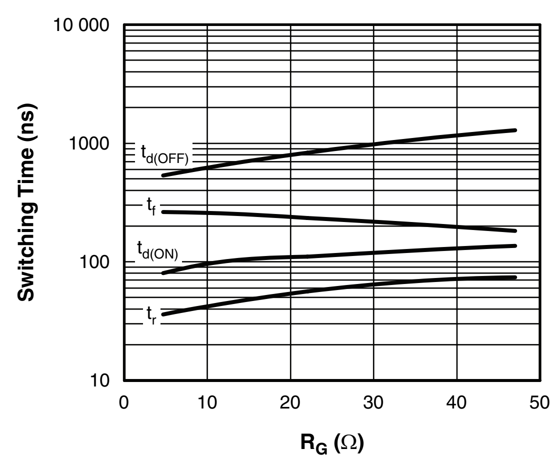


Fig. 31 - Typical Switching Time vs. R_G
T_J = 125 °C; L = 400 µH; V_{CE} = 600 V; I_{CE} = 25 A; V_{GE} = 15 V

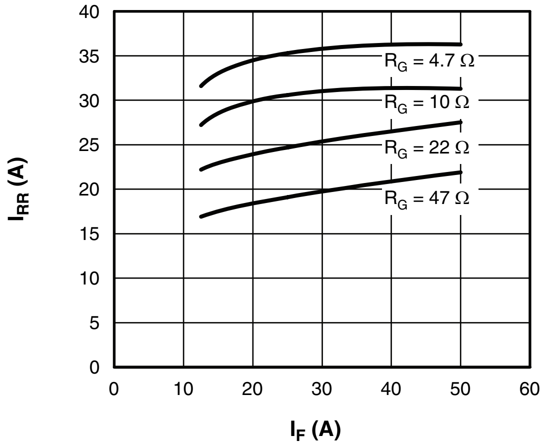


Fig. 32 - Typical Diode I_{RR} vs. I_F
T_J = 125 °C

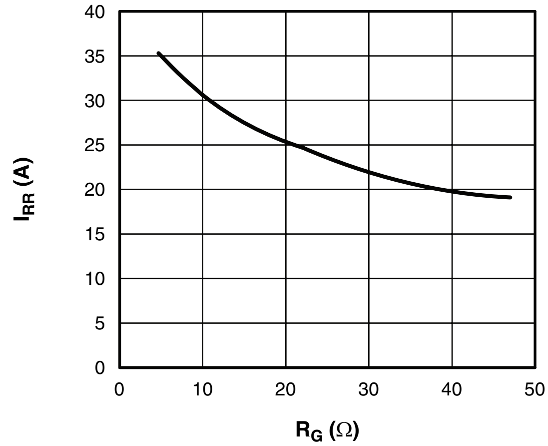


Fig. 33 - Typical Diode I_{RR} vs. R_G
T_J = 125 °C; I_F = 25 A

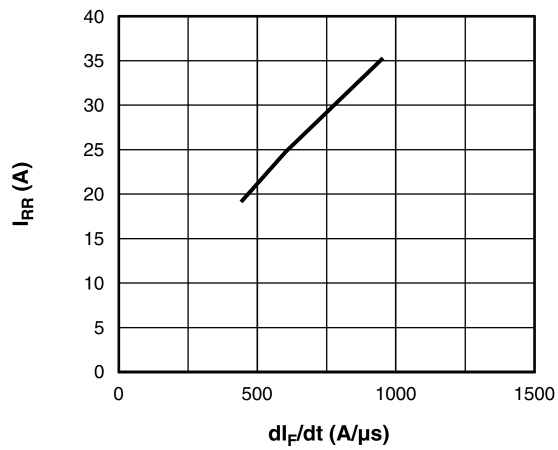


Fig. 34 - Typical Diode I_{RR} vs. dI_F/dt
V_{CC} = 600 V; V_{GE} = 15 V; T_J = 125 °C; I_F = 25 A

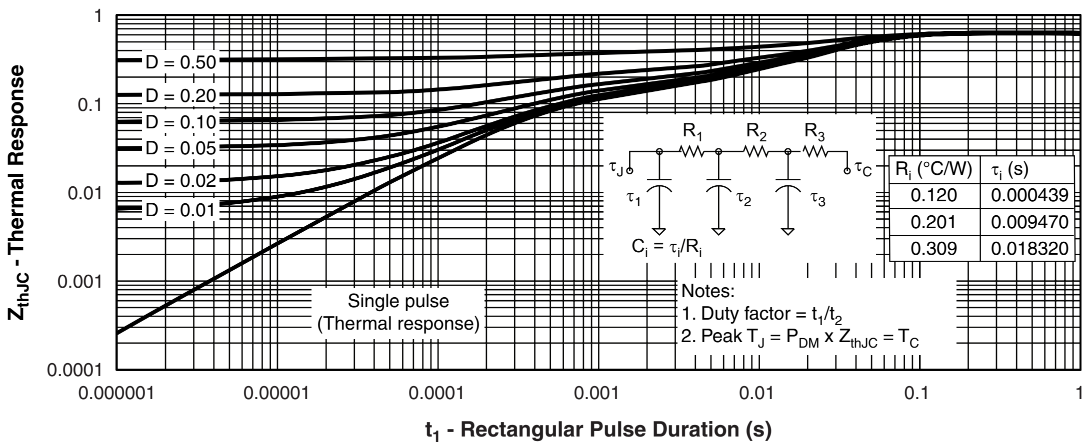


Fig. 35 - Maximum Transient Thermal Impedance, Junction to Case (Brake IGBT)

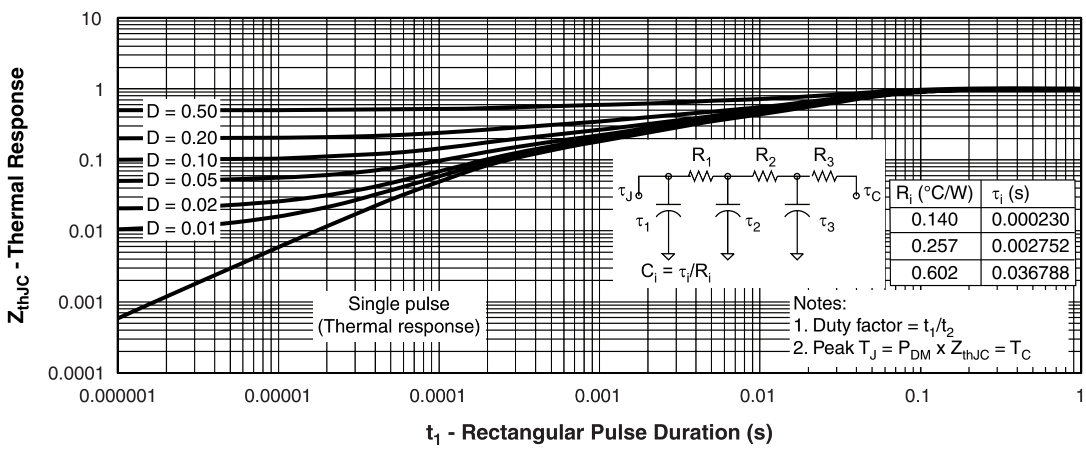


Fig. 36 - Maximum Transient Thermal Impedance, Junction to Case (Brake Diode)

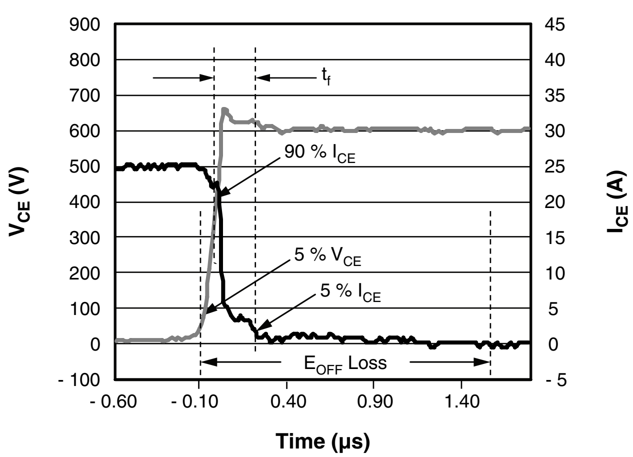


Fig. WF3 - Typical Turn-Off Loss Waveform at T_J = 125 °C using Fig. C.T.4

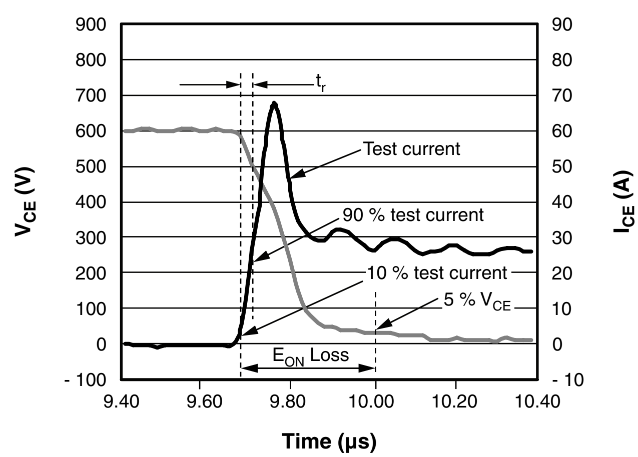


Fig. WF4 - Typical Turn-Off Loss Waveform at T_J = 125 °C using Fig. C.T.4

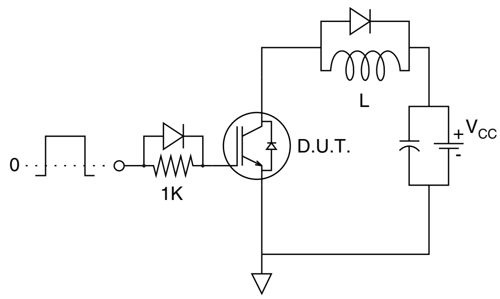


Fig. C.T.1 - Gate Charge Circuit (Turn-Off)

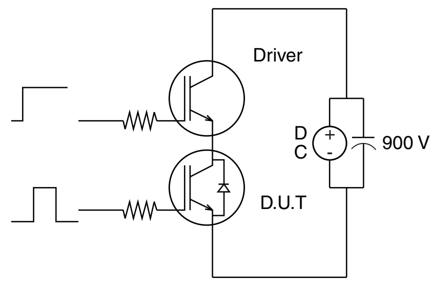


Fig. C.T.3 - S.C. SOA Circuit

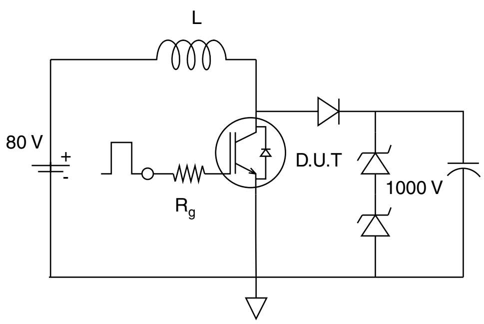


Fig. C.T.2 - RBSOA Circuit

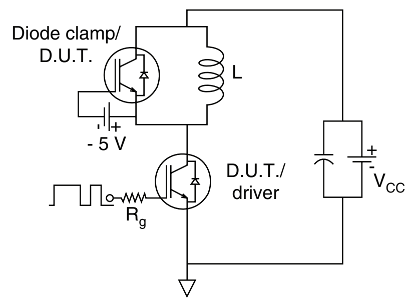


Fig. C.T.4 - Switching Loss Circuit

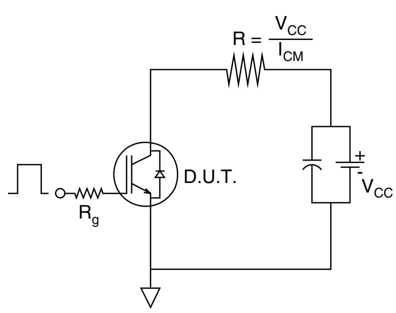


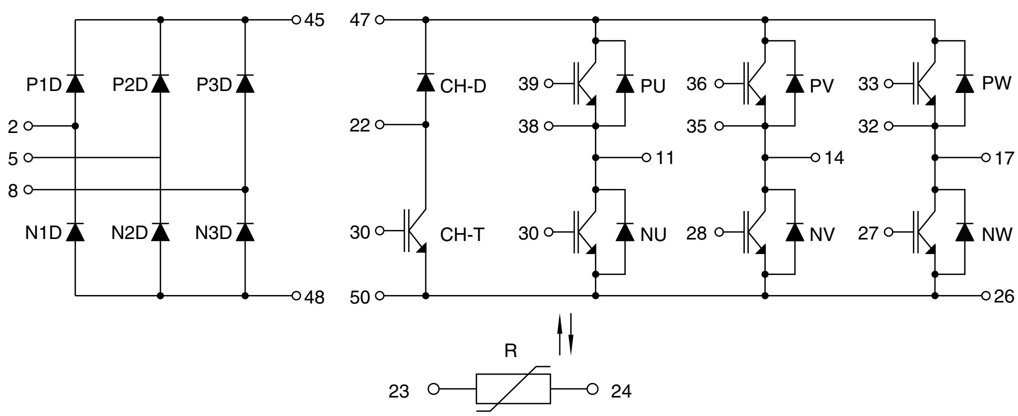
Fig. C.T.5 - Resistive Load Circuit

ORDERING INFORMATION TABLE

Device code	G	B	25	R	F	120	K
	1	2	3	4	5	6	7

1 - Insulated Gate Bipolar Transistor (IGBT)
2 - IGBT Generation 5 NPT
3 - Current rating (25 = 25 A)
4 - Circuit configuration
(R = Three phase bridge-brake-inverter with thermistor)
5 - Package (F = ECONO2)
6 - Voltage rating (120 = 1200 V)
7 - Ultrafast (Speed 8 to 60 kHz)

CIRCUIT CONFIGURATION



LINKS TO RELATED DOCUMENTS	
Dimensions	http://www.vishay.com/doc?95083
Part marking information	http://www.vishay.com/doc?95071

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All product specifications and data are subject to change without notice.

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